

# Test Report

No : CE/2006/B0252A    Date : 20061108    Page: 1 of 3

GREAT WALL SEMICONDUCTOR (GWS)  
7855 SOUTH RIVER PARKWAY, SUITE 122 TEMPE, AZ  
85284



Report on the submitted sample said to be N-CHANNEL LATERAL MOSFET.

Style/Item No : GWS12N07D / GWS12N22 / GWS12N30 / GWS15N15 /  
GWS15N30 / GWS20N15 / GWS24N07 / GWS24N08 /  
GWS6N60 / GWS6N90 / GWS8N60 / GWS9N90  
Sample Receiving Date : 2006/11/01  
Testing Period : 2006/11/01 TO 2006/11/08

=====  
**Test Requested** : In accordance with the RoHS Directive 2002/95/EC, and its amendment directives.

**Test Method** :  
(1) With reference to BS EN 1122:2001, Method B for Cadmium Content. Analysis was performed by ICP-AES.  
(2) With reference to US EPA Method 3050B for Lead Content. Analysis was performed by ICP-AES.  
(3) With reference to US EPA Method 3052 for Mercury Content. Analysis was performed by ICP-AES.  
(4) With reference to US EPA Method 3060A & 7196A for Hexavalent Chromium. Analysis was performed by UV/Vis Spectrometry.  
(5) With reference to US EPA 3540C for PBB/PBDE Content. Analysis was performed by GC/MS and screening via US EPA 3550C with HPLC/DAD/MS.

**Test Result(s)** : Please refer to next page(s).

  
Daniel Yeh, M.R. / Operation Manager  
Signed for and on behalf of  
SGS TAIWAN LTD.

# Test Report

No : CE/2006/B0252A    Date : 20061108    Page: 2 of 3

GREAT WALL SEMICONDUCTOR (GWS)  
7855 SOUTH RIVER PARKWAY, SUITE 122 TEMPE, AZ  
85284



Test results by chemical method (Unit: mg/kg)

Test Item (s):	Method (Refer to)	Result	MDL
		No.1	
Cadmium (Cd)	(1)	n.d.	2
Lead (Pb)	(2)	28.5	2
Mercury (Hg)	(3)	n.d.	2
Hexavalent Chromium (CrVI)	(4)	n.d.	2
<b>Sum of PBBs</b>	(5)	n.d.	-
Monobromobiphenyl		n.d.	5
Dibromobiphenyl		n.d.	5
Tribromobiphenyl		n.d.	5
Tetrabromobiphenyl		n.d.	5
Pentabromobiphenyl		n.d.	5
Hexabromobiphenyl		n.d.	5
Heptabromobiphenyl		n.d.	5
Octabromobiphenyl		n.d.	5
Nonabromobiphenyl		n.d.	5
Decabromobiphenyl		n.d.	5
<b>Sum of PBDEs (Mono to Nona) (Note 4)</b>		n.d.	-
Monobromobiphenyl ether		n.d.	5
Dibromobiphenyl ether		n.d.	5
Tribromobiphenyl ether		n.d.	5
Tetrabromobiphenyl ether		n.d.	5
Pentabromobiphenyl ether		n.d.	5
Hexabromobiphenyl ether		n.d.	5
Heptabromobiphenyl ether		n.d.	5
Octabromobiphenyl ether		n.d.	5
Nonabromobiphenyl ether		n.d.	5
Decabromobiphenyl ether		n.d.	5
<b>Sum of PBDEs (Mono to Deca)</b>		n.d.	-

### Test Part Description:

NO.1 : N-CHANNEL LATERAL MOSFET

Note : 1. mg/kg = ppm

2. n.d. = Not Detected

3. MDL = Method Detection Limit

4. Sum of Mono to NonaBDE & according to 2005/717/EC DecaBDE is exempt.

5. "-" = Not Regulated

## Test Report

No : CE/2006/B0252A    Date : 20061108    Page: 3 of 3

GREAT WALL SEMICONDUCTOR (GWS)  
7855 SOUTH RIVER PARKWAY, SUITE 122 TEMPE, AZ  
85284



\*\* End of Report \*\*